

WSP4807

Dual P-Ch MOSFET

General Description

The WSP4807 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSP4807 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

Product Summery

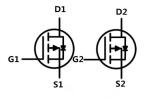
BVDSS	RDSON	ID
-30V	33mΩ	-6.5A

Applications

Power Management in Notebook Computer,
Portable Equipment and Battery Powered
Systems.

SOP-8 Pin Configuration





Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I₀@T₀=25℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-6.5	A
I _D @T _C =100℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-5.3	A
I _{DM}	Pulsed Drain Current ²	-20	A
P₀@T₀=25℃	Total Power Dissipation ³	1.5	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction-Ambient ¹		85	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹		36	°C/W

Absolute Maximum Ratings



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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=-1mA		-0.		V/℃
D	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-3A		33	46	V V/°C mΩ V uA
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-1.5A		53	72	
V _{GS(th)}	Gate Threshold Voltage		-1.0	-		V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient			4.		mV/℃
1	Drain Source Lookage Current	$V_{\text{DS}}\text{=-24V}$, $V_{\text{GS}}\text{=}0\text{V}$, $T_{\text{J}}\text{=}25^\circ\!\mathrm{C}$		-	-1	
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-24V , V_{GS} =0V , TJ=55 $^{\circ}\mathrm{C}$		-	-5	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm20V$, $V_{DS}=0V$		-	±100	nA
gfs	orward Transconductance	V _{DS} =-5V , I _D =-3A		5		S
Rg	Gate Resistance V _{DS} =0V , V _{GS} =0V , f=1MHz			24	48	Ω
Qg	Total Gate Charge (-4.5V)			6.2		
Q _{gs}	Gate-Source Charge	V_{DS} =-20V , V_{GS} =-4.5V , I_{D} =-5A		2.5		nC
Q _{gd}	Gate-Drain Charge			3.3		
T _{d(on)}	Turn-On Delay Time			9.2		
Tr	Rise Time	V _{DD} =-15V , V _{GS} =-10V , R _G =3.3Ω I _D =-1Α		16.5		
T _{d(off)}	Turn-Off Delay Time			21.3		115
T _f	Fall Time			21.5		
Ciss	Input Capacitance			640		
C _{oss}	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		270		pF
C _{rss}	Reverse Transfer Capacitance			103		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current			-6.5	А
I _{SM}	Pulsed Source Current ^{2,4}			-	-12	А
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃		-	-1.2	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10 sec.

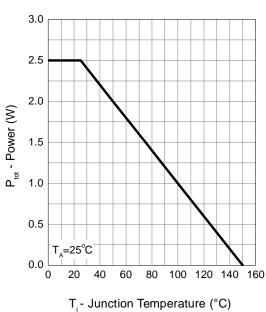
2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%

3.The power dissipation is limited by 150 $^\circ\! \mathbb C$ junction temperature

4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

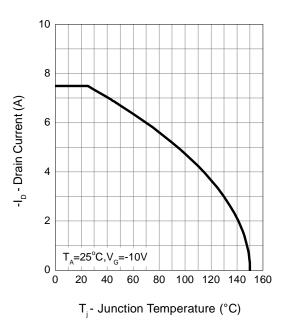


Typical Operating Characteristics

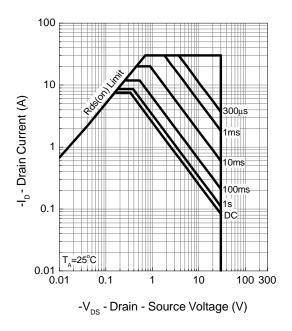


Power Dissipation

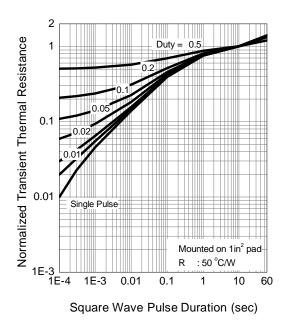
Drain Current



Safe Operation Area

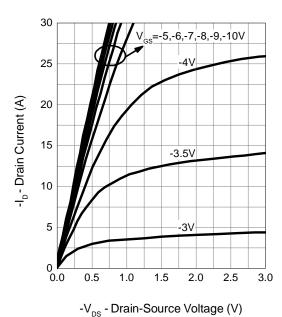


Thermal Transient Impedance



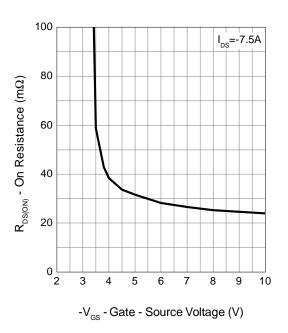


Typical Operating Characteristics (Cont.)

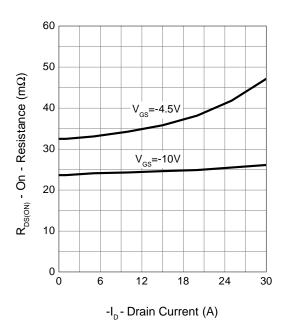


Output Characteristics

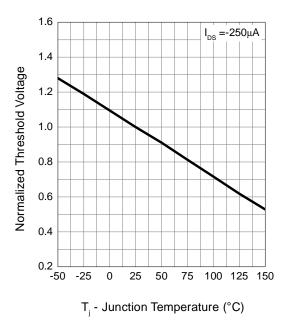
Gate-Source On Resistance



Drain-Source On Resistance

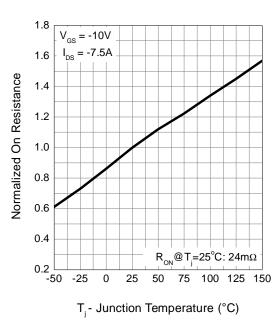


Gate Threshold Voltage



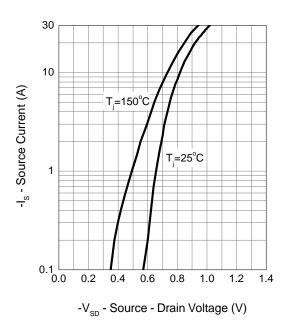


Typical Operating Characteristics (Cont.)

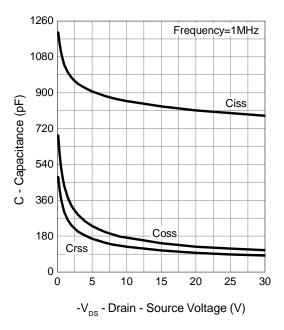


Drain-Source On Resistance

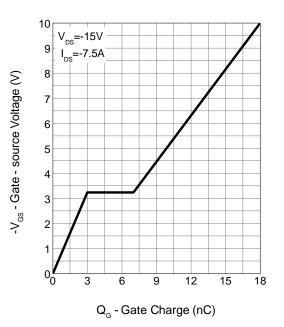
Source-Drain Diode Forward



Capacitance



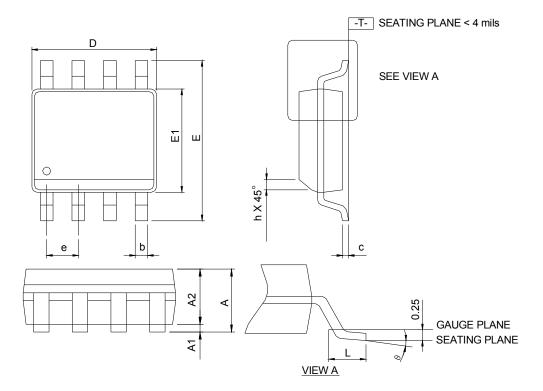
Gate Charge



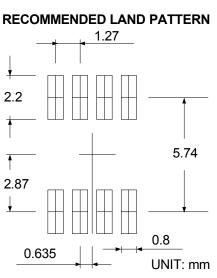


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Package Information SOP-8



Ş		SO	P-8		
Ş¥ MBO	MILLIMETERS		INCHES		
2	MIN.	MAX.	MIN.	MAX.	
А		1.75		0.069	
A1	0.10	0.25	0.004	0.010	
A2	1.25		0.049		
b	0.31	0.51	0.012	0.020	
С	0.17	0.25	0.007	0.010	
D	4.80	5.00	0.189	0.197	
Е	5.80	6.20	0.228	0.244	
E1	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
h	0.25	0.50	0.010	0.020	
L	0.40	1.27	0.016	0.050	
θ	0 °	8 °	0°	8°	



Note: 1. Follow JEDEC MS-012 AA.

2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.

 Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

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